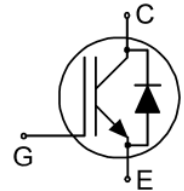


IGBT chip with monolithically integrated diode in packages offering space saving advantage
Features:

TRENCHSTOP™ Reverse Conducting (RC) technology for 600V applications offering:

- Optimised V_{CEsat} and V_F for low conduction losses
- Smooth switching performance leading to low EMI levels
- Very tight parameter distribution
- Operating range of 1 to 20kHz
- Maximum junction temperature 175°C
- Short circuit capability of 5µs
- Best in class current versus package size performance
- Qualified according to JEDEC for target applications
- Complete product spectrum and PSpice Models:

<http://www.infineon.com/igbt/>


Applications:

Motor drives

Used for:

Discrete components and molded modules

Chip Type	V_{CE}	I_{Cn}	Die Size	Package
IGC05R60DE	600V	6A	2.21 x 2.19 mm ²	sawn on foil

Mechanical Parameters

Raster size	2.21 x 2.19		mm ²
Emitter pad size	see chip drawing		
Gate pad size	see chip drawing		
Area: total / active IGBT / active Diode	4.84 / 2.219 / 0.477		
Thickness	70		µm
Wafer size	200		mm
Max.possible chips per wafer	5775		
Passivation frontside	Photoimide		
Pad metal	3200 nm AlSiCu		
Backside metal	Ni Ag –system		
Die bond	Electrically conductive epoxy glue and soft solder (temperature budget: 290°C for 1min. or 260°C for 1.5min.)		
Wire bond	Al, <250µm		
Reject ink dot size	Ø 0.65mm ; max 1.2mm		
Storage environment	for original and sealed MBB bags	Ambient atmosphere air, Temperature 17°C – 25°C, < 6 month	
	for open MBB bags	Acc. to IEC62258-3: Atmosphere >99% Nitrogen or inert gas, Humidity <25%RH, Temperature 17°C – 25°C, < 6 month	

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter voltage, $T_{vj} = 25\text{ °C}$	V_{CE}	600	V
DC collector current, limited by $T_{vj, max}$	I_C	1)	A
Pulsed collector current, t_p limited by $T_{vj, max}$	$I_{C, puls}$	18	A
Gate emitter voltage	V_{GE}	± 20	V
Junction temperature range	$T_{vj, max}$	-40 ... +175	°C
Operating junction temperature	$T_{vj, op, max}$	-40 ... +175	°C
Short circuit data ²⁾³⁾ $V_{GE} = 15V, V_{CC} = 400V, T_{vj} = 150\text{ °C}$	t_{SC}	5	μs
Safe operating area IGBT ²⁾³⁾	$I_{C, max} = 12A, V_{CE, max} = 600V, T_{vj, op} \leq T_{vj, op, max}$		
Safe operating area Diode ²⁾	$I_{F, max} = 12A, V_{R, max} = 600V,$ $P_{max} = 4.8\text{ kW}, T_{vj, op} \leq T_{vj, op, max}$		

1) depending on thermal properties of assembly

2) not subject to production test - verified by design/characterization

3) allowed number of short circuits: <1000; time between short circuits: >1s

Static Characteristics (tested on wafer), $T_{vj} = 25\text{ °C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-Emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=0.2\text{ mA}$	600			V
Collector-Emitter saturation voltage	V_{CEsat}	$V_{GE}=15V, I_C=6A$		1.65	2.1	
Diode Forward Voltage	V_F	$V_{GE}=0V, I_F=6A$		1.7	2.1	
Gate-Emitter threshold voltage	$V_{GE(th)}$	$I_C=0.11\text{ mA}, V_{GE}=V_{CE}$	4.3	5	5.7	
Zero gate voltage collector current	I_{CES}	$V_{CE}=600V, V_{GE}=0V$			40	μA
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V$			100	nA
Integrated gate resistor	r_G			none		Ω

Electrical Characteristics (not subject to production test - verified by design / characterization)

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-Emitter saturation voltage	$T_{vj} = 175\text{ °C}$ V_{CEsat}	$V_{GE}=15V, I_C=6A$		1.85		V
Input capacitance	C_{ies}	$V_{CE}=25V,$ $V_{GE}=0V, f=1\text{ MHz}$ $T_{vj} = 25\text{ °C}$		470		pF
Output capacitance	C_{oes}			24		
Reverse transfer capacitance	C_{res}			14		